SMBF Schottky Barrier Rectifier Diode　肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:SMBF

■Maximum Rating 最大额定值

(T$_A$=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	SS54LBF	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	40	V
DC Reverse Voltage 直流反向电压	V_R	40	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	28	V
Forward Rectified Current 正向整流电流	I_F	5	A
Peak Surge Current 峰值浪涌电流	I_{FSM}	120	A
Thermal Resistance J-A 结到环境热阻	$R_{θJA}$	70	℃/W
Junction Temperature 结温	T_J	125	℃
Storage Temperature 储藏温度	T_{stg}	-55to+150℃	℃

■Electrical Characteristics 电特性

(T$_A$=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	SS54LBF	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.48	V	I_F=5A
Reverse Current 反向电流	I_R(25℃) (100℃)	0.2 50	mA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D	380	pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

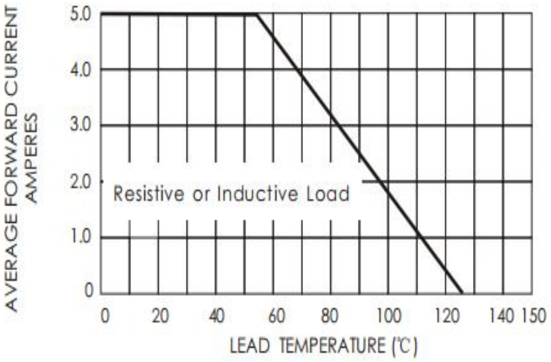


Figure 1: Forward Current Curve

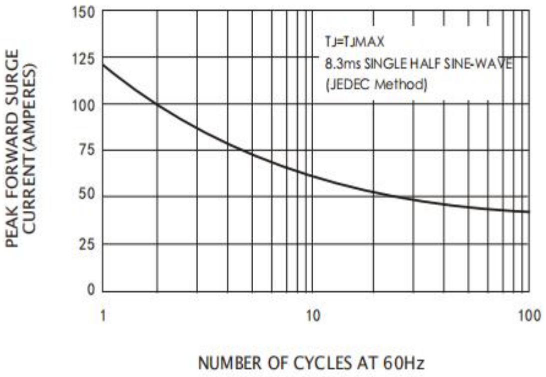


Figure 2: Forward Surge Current Curve

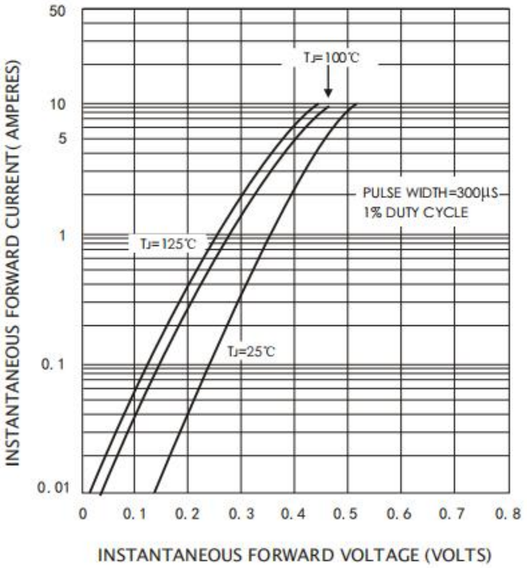


Figure 3: Forward Characteristics

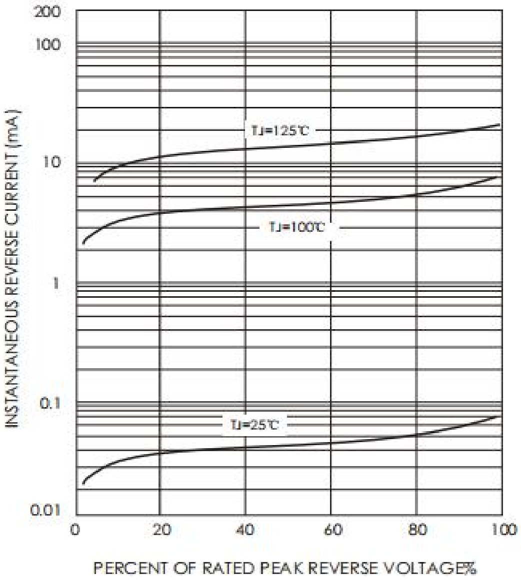


Figure 4: Reverse Characteristics

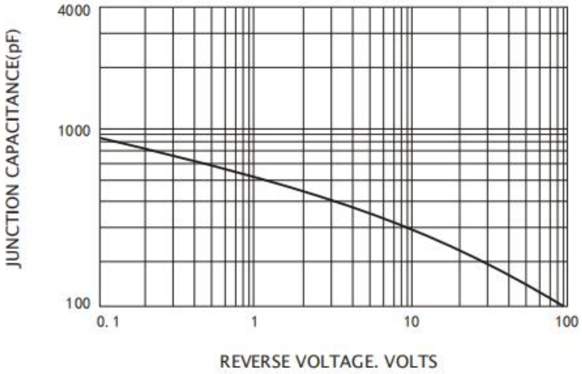
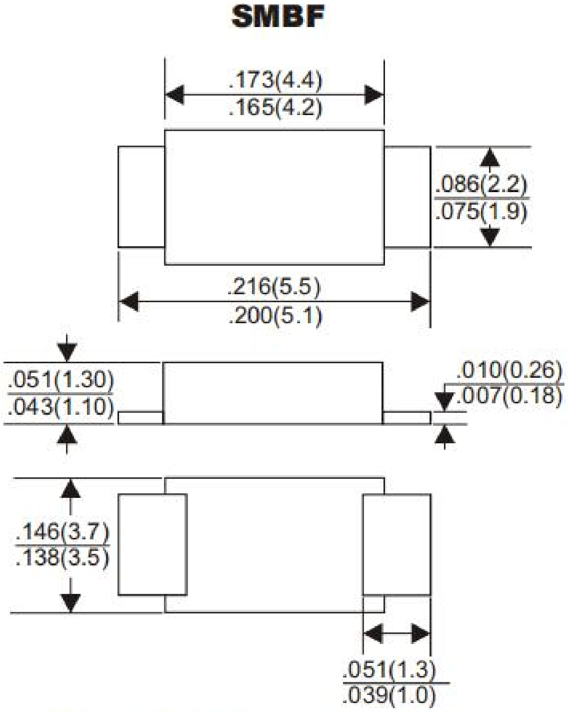


Figure 5: Capacitance Characteristics

■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)